

US-PAT-NO: 5365334

DOCUMENT-IDENTIFIER: US 5365334 A

TITLE: Micro photorefectance semiconductor wafer analyzer

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Detailed Description Text - DETX (8):

Gallium Arsenide, Aluminum Gallium Arsenide, and other materials have a valence-conduction band-gap, E.sub.g, whose conduction properties are dominated by valence to conduction band transitions at critical points. In semiconductors, this band-gap is inferred by measuring the fundamental, optical absorption edge of the material. The fundamental, optical absorptive edge shifts under the influence of an applied electric field. This shift in the absorptive edge--called the Franz-Keldysh effect--is the basis for optical characterization techniques such as electroabsorption and electroreflectance. These techniques require that the test apparatus make electric contact with the sample under test.

U.S. Patent

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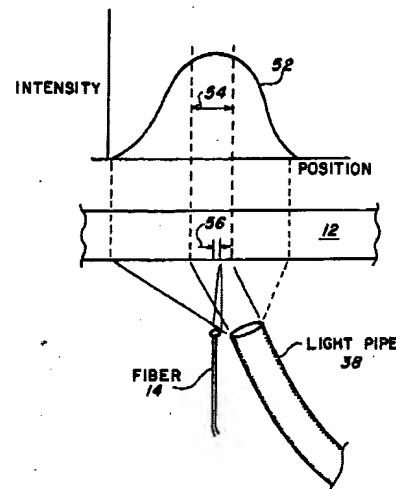


FIG. 2

	Document ID	Kind Codes	Source	Issue Date	Pages	
1	US 6468347 B1		USPAT	20021022	33	Metho
2	US 6356381 B1		USPAT	20020312	16	Multi
3	US 5365334 A		USPAT	19941115	10	Micro
4	US 4790669 A		USPAT	19881213	12	Spect
5	US 4378496 A		USPAT	19830329	10	Curre
6	US 4286215 A		USPAT	19810825	8	Metho
7	US 3871017 A		USPAT	19750311	19	High-